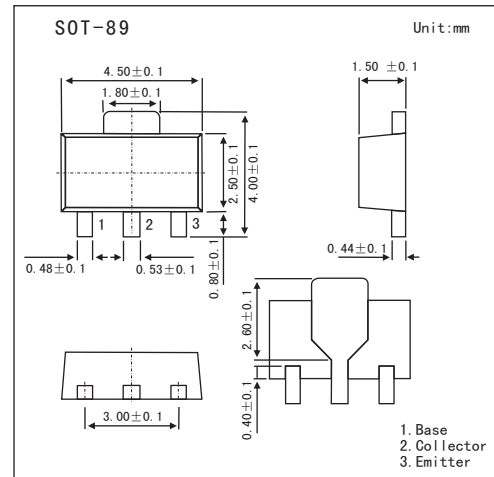


Silicon NPN Triple Diffused 2SC3380

■ Features

- High frequency high voltage amplifier
- High voltage switch



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	300	V
Collector-emitter voltage	V _{CEO}	300	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	100	mA
Total power dissipation	P _C *	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _c = 10 μA, I _E = 0	300			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _c = 1 mA, I _B = 0	300			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10 μA, I _c = 0	5			V
Collector cutoff current	I _{CEO}	V _{CB} = 250V, I _B = 0			1.0	μA
Collector to emitter saturation voltage	V _{CE(sat)}	I _c = 20 mA, I _B = 2 mA			1.5	V
DC current gain	h _{FE}	V _{CE} = 20V, I _c = 20mA	30		200	
Transition frequency	f _T	V _{CE} = 20V, I _c = 20mA		80		MHz
Output Capacitance	C _{ob}	V _{CB} = 20 V, I _E = 0, f = 1.0 MHz			4	pF

■ Marking

Marking	AS